



JUNCTION FIELD EFFECT TRANSISTOR 2SK3653

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK3653 is suitable for converter of ECM.

FEATURES

- Compact package
- High forward transfer admittance 1000 μS TYP. (IDSS = 100 μA) 1600 μS TYP. (IDSS = 200 μA)
- Includes diode and high resistance at G S

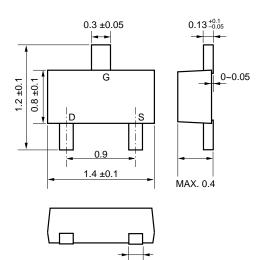
ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3653	3pinXSOF (0814)		

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

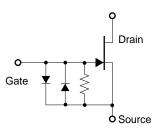
Drain to Source Voltage Note1	VDSX	20	V
Gate to Drain Voltage	Vgdo	-20	V
Drain Current	lo	10	mA
Gate Current	lg	10	mA
Total Power Dissipation Note2	Ρτ	80	mW
Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	-55 to +125	°C

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT

0.2 +0.



Notes 1. Vgs = -1.0 V

2. Mounted on ceramic substrate of 3.0 cm² x 0.64 mm

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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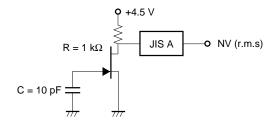
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	DSS1	$V_{DS} = 2.0 V, V_{GS} = 0 V$	38		570	μA
Zero Gate Voltage Drain Cut-off Current	IDSS2	$V_{DS} = 5.0 V, V_{GS} = 0 V$	40		600	μA
Gate Cut-off Voltage	VGS(off)	$V_{DS} = 5.0 \text{ V}, \text{ Id} = 1.0 \ \mu\text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y₁s₁	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 30 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	yfs2	$V_{DS} = 5.0 V$, $V_{GS} = 0 V$, $f = 1.0 \text{ kHz}$	350			μS
Input Capacitance	Ciss	$V_{DS} = 5.0 V$, $V_{GS} = 0 V$, $f = 1.0 MHz$		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

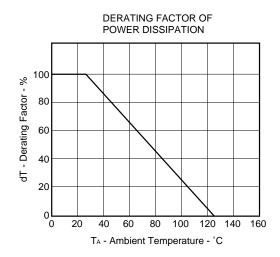
IDSS RANK

MARKING	J2	J3	J4	J5	J6	J7
IDSS1 (μΑ) VDS = 2.0 V	38 to 65	56 to 105	85 to 170	140 to 280	185 to 425	280 to 570

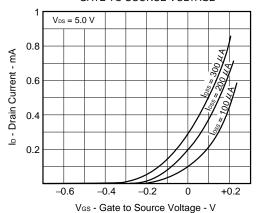
NOISE VOLTAGE TEST CIRCUIT



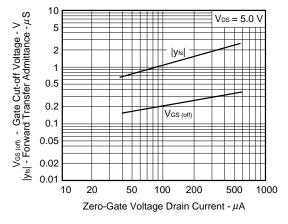
TYPICAL CHARACTERISTICS (TA = 25°C)

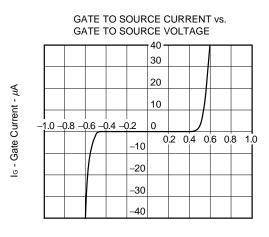




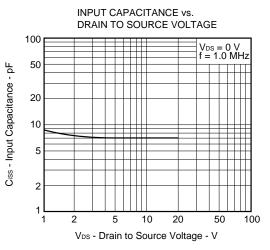


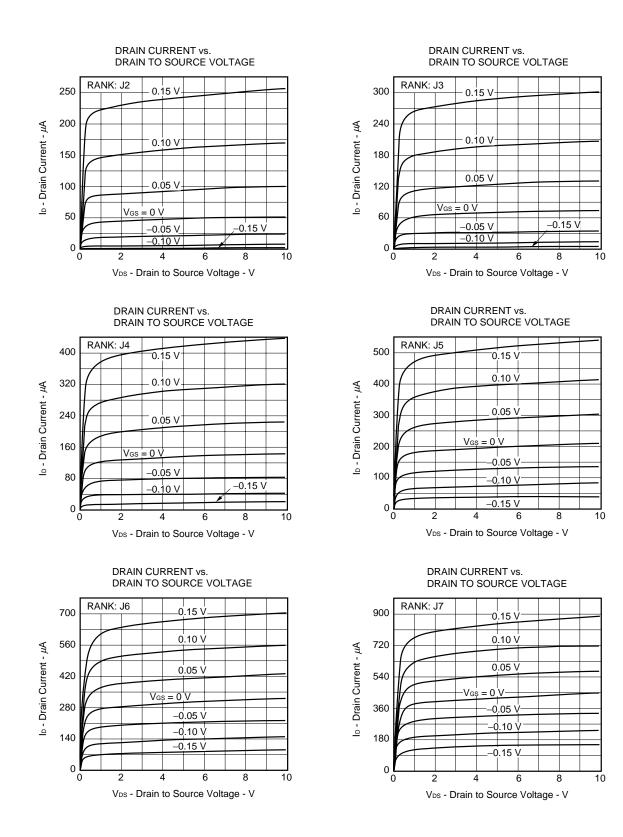






VGS - Gate to Source Voltage - V





[MEMO]

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